

Silicon NPN Power Transistors

2SD1479

DESCRIPTION

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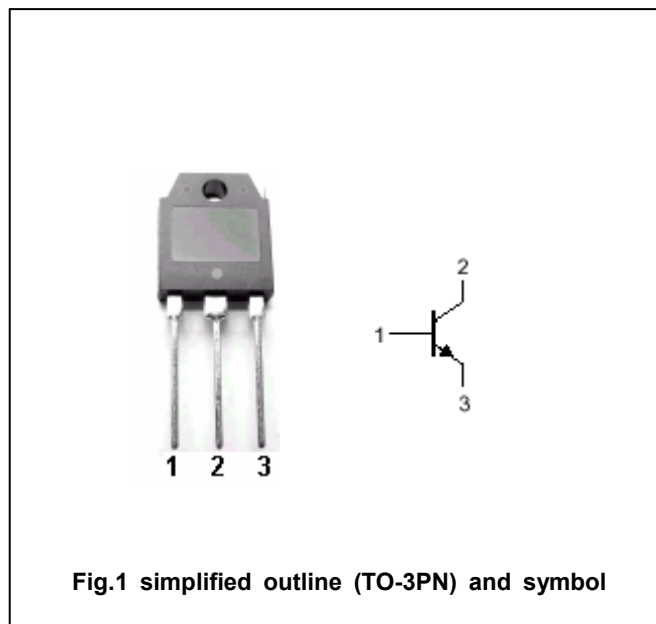
- With TO-3PN package
- High voltage ,high reliability
- High speed switching
- Wide area of safe operation

APPLICATIONS

- For horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	700	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current (DC)		2.5	A
I _{CM}	Collector current (Pulse)		6	A
I _{BM}	Base current (Pulse)		2.5	A
P _C	Collector power dissipation	T _C =25℃	80	W
T _j	Junction temperature		150	℃
T _{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25°C unless otherwise specified

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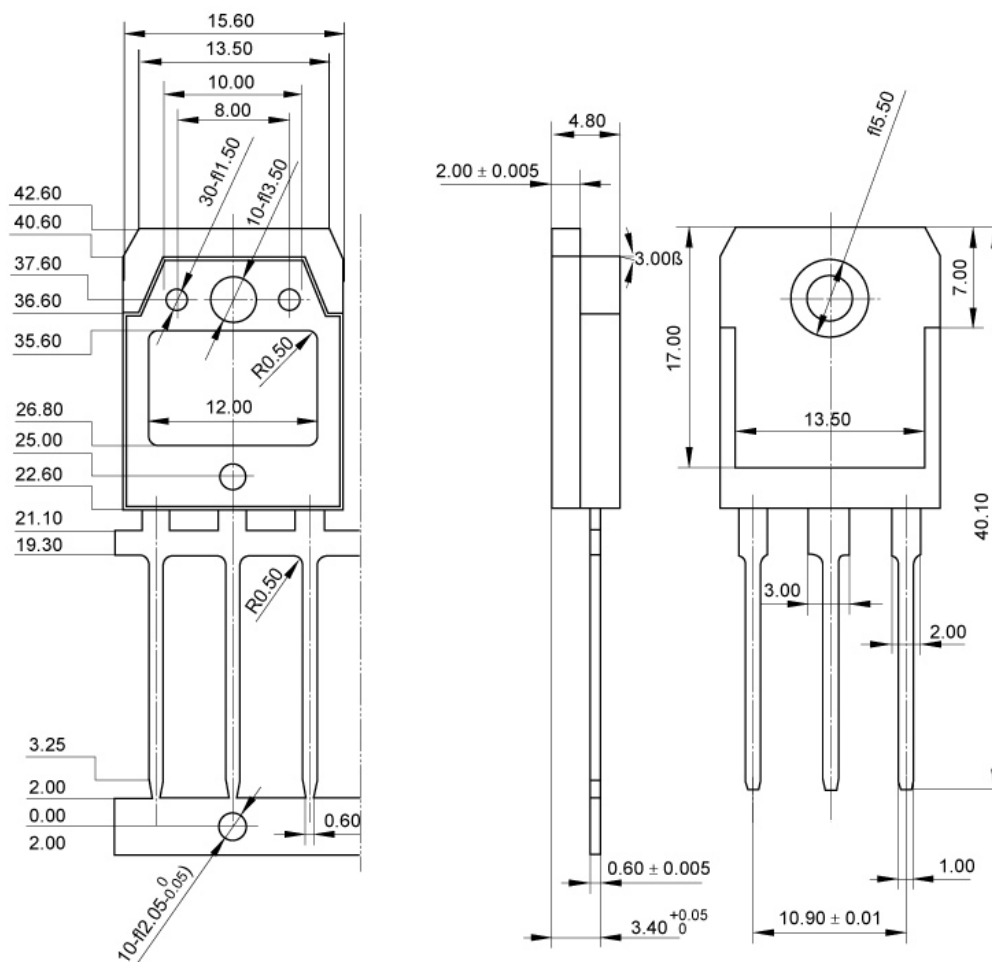
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA; I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=2A; I_B=1A$			5.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=2A; I_B=1A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=750V; I_E=0$			50	μA
		$V_{CB}=1500V; I_E=0$			1.0	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V; I_C=0$			50	μA
h_{FE}	DC current gain	$I_C=2A; V_{CE}=5V$	2		5	
t_s	Storage time	$I_C=2.5A$ $I_{Bend}=1.1A, L_B=10\mu H$			9.0	μs
t_f	Fall time				1.0	μs

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PACKAGE OUTLINE

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Fig.2 outline dimensions (unindicated tolerance: ± 0.10 mm)